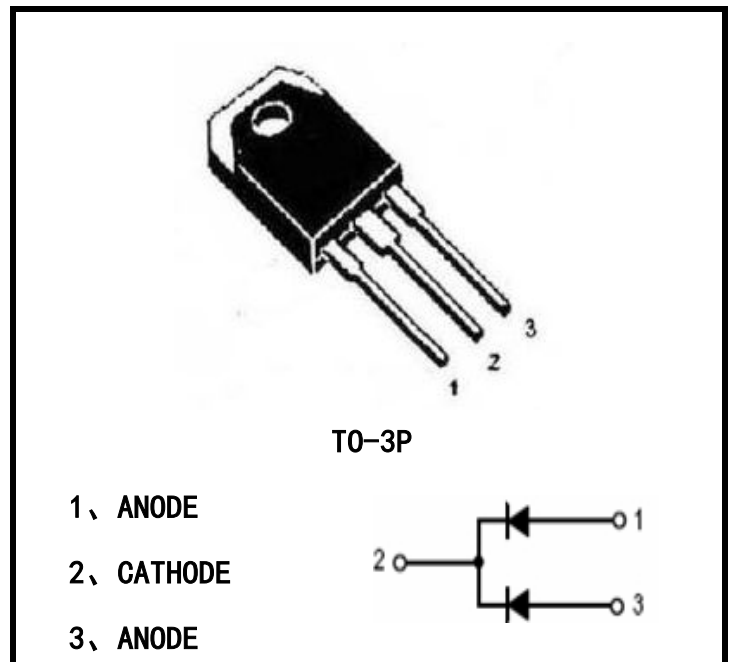


FEATURES

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

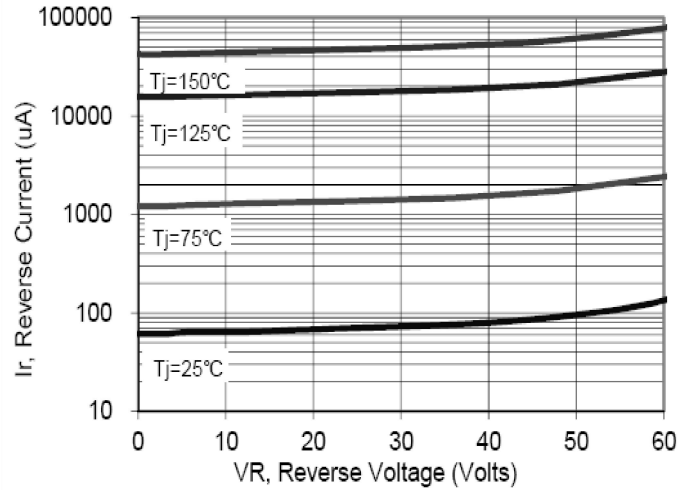
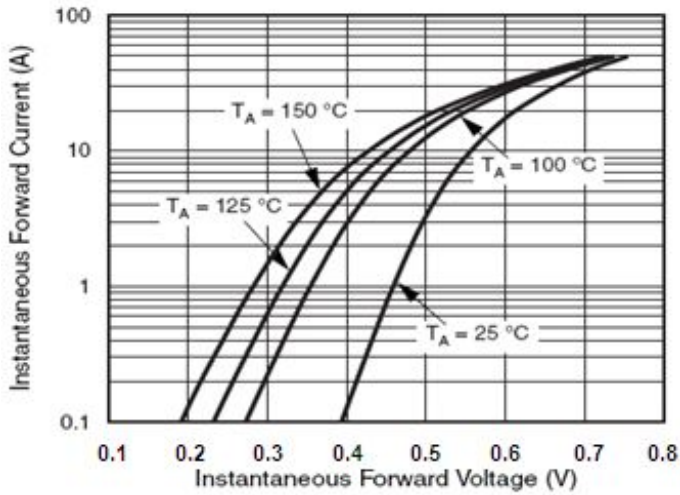
PACKAGE



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

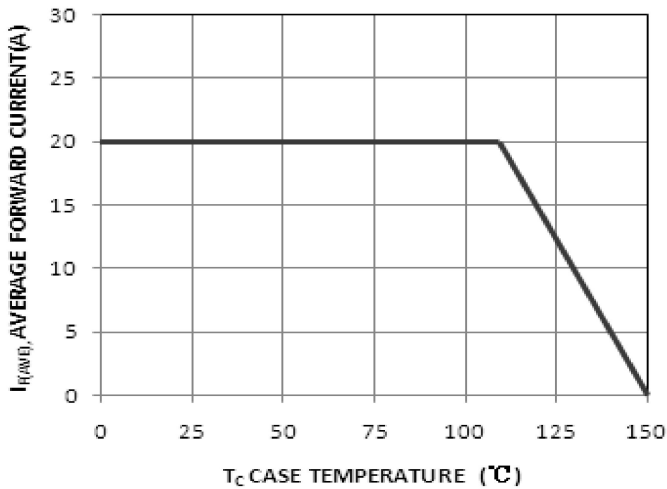
Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	45	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Average Rectified Output Current	I _{F(per leg)}	20	A
	I _{F(Total)}	40	
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I _{FSM}	350	A
Maximum Instantaneous Forward Voltage @IF=20A, TC=25°C	V _F	0.65	V
		@IF=20A, TC=125°C	
Peak Reverse Current @Tc=25 °C	I _R	0.15	mA
at Rated DC Blocking Voltage @Tc=125°C		100	
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C
Maximum Thermal Resistance	θ _{JC}	1.4	°C/W
	θ _{JA}	60	

Characteristics Curves



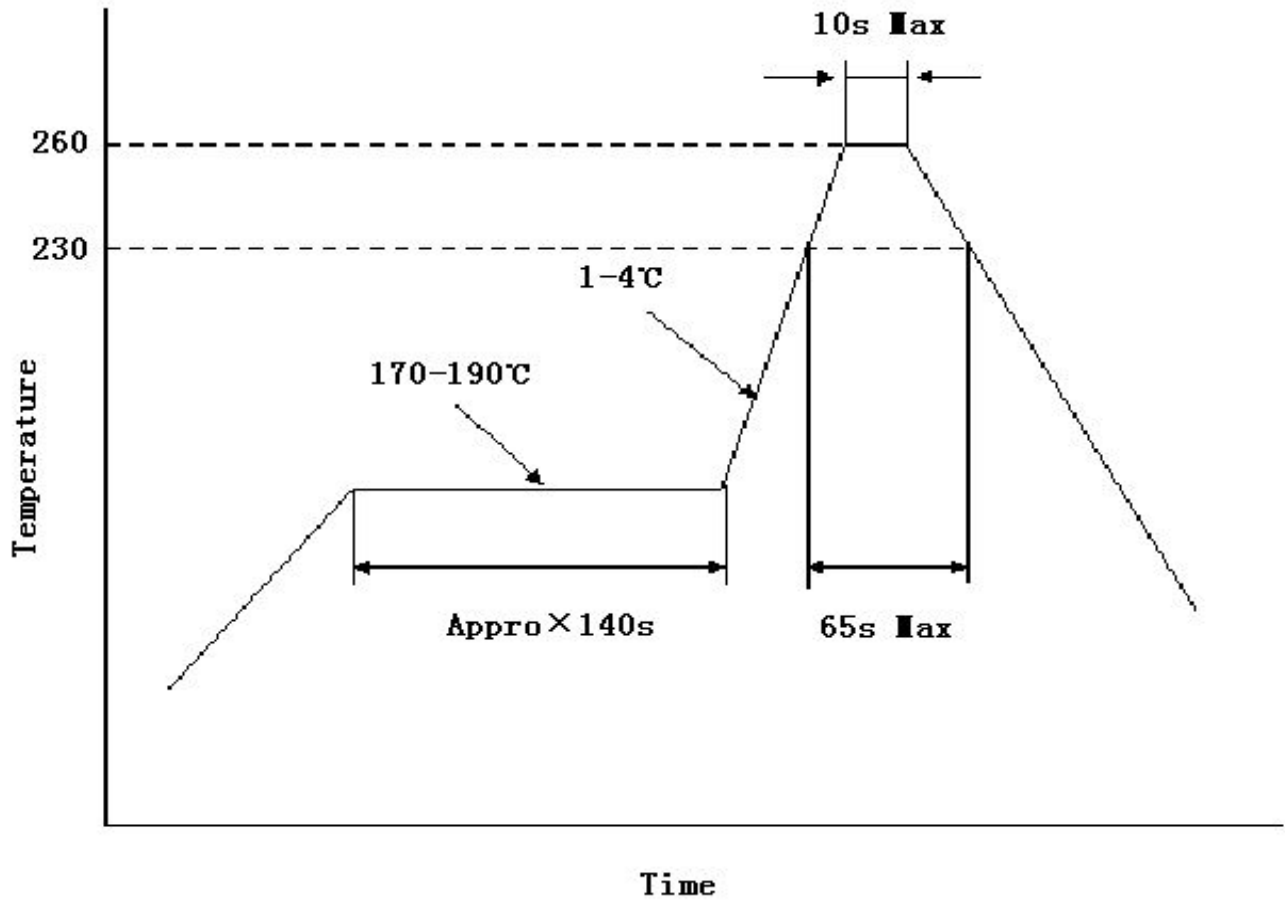
Typical Forward Voltage Per Diode

Typical Reverse Current Per Diode



Average Forward Current vs. Case Temperature Per Diode

■ Reflow Soldering Temperature Profile



TO-3P MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	15.2		15.8	J	3.3		3.9
B	12.2		12.8	K	1.8		2.2
C	9.7		10.3	L	2.8		3.2
D	3	3.2	3.4	M	0.8		1.2
E	4.7		5.3	N	5.2	5.45	5.7
F	19		19.6	O	4.6		5.2
G	17.8		18.4	P	1.8		2.3
H	13.6		14.3	Q	2.6		3.3
I	19.5		20.5	R	0.5		0.7

